

Figure 1: Sketch of the III-V laser stack grown in a pocket on a silicon photonics wafer with the active region aligned to a silicon nitride waveguide.

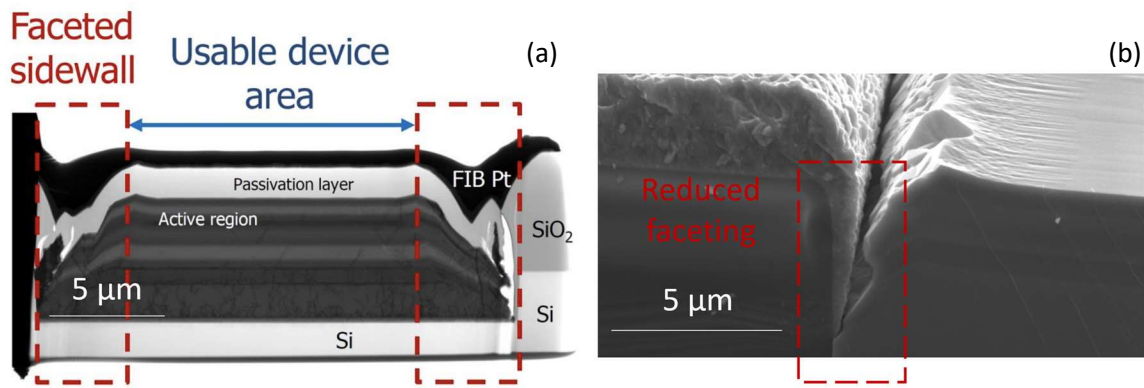


Figure 2: Cross-sectional scanning electron microscope images showing a laser grown under conventional growth conditions with a large gap (a) and a laser grown with a selective buffer and a reduced gap (b).

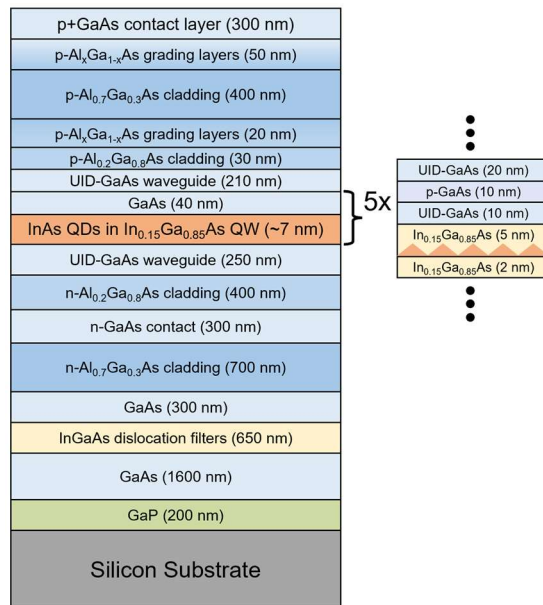


Figure 3: Layer stack of the III-V InAs quantum dot laser structure grown on silicon.